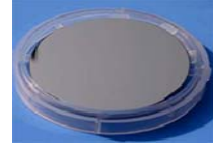




Silicon Crystal & Compound Semiconductor

Indium Arsenide (InAs) Substrate

Indium Arsenide (InAs) Substrate is compound by high purity Indium and Arsenic elements, grown by Liquid Encapsulated Czochralski (LEC) method, which can be adopted in optoelectronics industry, such as fabrication of InAsSb or InAsPSb heterogeneous materials or infrared device between 2-12 μ m wave length. 2" 3" 4" is available.



No.	Items	Standard Specifications		
1	Size	2"	3"	4"
2	Diameter mm	50.8 \pm 0.5	76.2 \pm 0.5	100 \pm 0.5
3	Growth Method	LEC	LEC	LEC
4	Conductivity	P/N	P/N	P/N
5	Orientation	<100>, <111>		
6	Thickness μ m	500 \pm 25	600 \pm 25	800 \pm 25
7	Flats Option	EJ or as per SEMI		
8	Orientation Flat mm	16 \pm 2	22 \pm 2	32.5 \pm 2
9	Identification Flat mm	8 \pm 1	11 \pm 1	18 \pm 1
10	Hall Mobility $\text{cm}^2/\text{v.s}$	600-2E4 or as required		
11	Carrier Concentration atoms/cm^3	\leq 5E16 or as required		
12	TTV μ m max	10	10	10
13	Bow μ m max	10	10	10
14	Warp μ m max	15	15	15
15	EPD cm^{-2} max	5E4	5E4	5E4
16	Surface Finish	P/E, P/P, E/E	P/E, P/P, E/E	P/E, P/P, E/E
17	Packing	Single wafer container inside, carton box outside.		

Indium Phosphide (InP) Substrate

Indium Phosphide (InP) Substrate is compound by high purity Indium and Phosphorus elements, grown by Vertical Gradient Freeze (VGF) method, with high hall mobility, radiation endurance and thermal conduction characteristics, which can be widely used for Opto-electronic civil industries, such as micro-wave or optical-fiber communication, satellite navigation and so on. 2" 3" and 4" is available.



No.	Items	Standard Specifications		
1	Size	2"	3"	4"
2	Diameter mm	50.8 \pm 0.5	76.2 \pm 0.5	100 \pm 0.5
3	Growth Method	VGF	VGF	VGF
4	Conductivity	P/N/Semi-insulating		
5	Orientation	<100>, <111>		
6	Thickness μ m	300 \pm 25	500 \pm 25	600 \pm 25
7	Resistivity $\Omega.\text{cm}$	$>$ 5E16, Semi-insulating/Fe		
8	Hall Mobility $\text{cm}^2/\text{v.s}$	50-4000 or as required		
9	Carrier Concentration atoms/cm^3	(0.6-6)E18 or as required		
10	TTV μ m max	10	10	10
11	Bow μ m max	10	10	10
12	Warp μ m max	15	15	15
13	Surface Finish	P/E, P/P, E/E	P/E, P/P, E/E	P/E, P/P, E/E
14	Packing	Single wafer container inside, carton box outside.		

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